

## **Developer for AR resists**

## AR 300-40 metal ion-free developer

For the development of photoresists and novolac-based e-beam resist films

## Characterisation

- metal ion-free aqueous-alkaline solutions for the processing of photo/ e-beam resists
- reduce the risk of metal ion contamination at the substrate surface
- residue-free development
- metal ion content < 0.1 ppm
- main component TMAH

Properties					
Parameter / AR	300- 44	300- 46	300- 47	300- 475	
Normality (n)	0.26	0.24	0.20	0.17	
Density at 20 °C (g/cm3)	0.99				
Surface tension (mN/m)	32 max.				
Filtration (µm)	0.2				
Storage temperatre (°C)	10-22				

Development recommendations	optimally suited	suited						
AR-resists AR-resists		AR 300-44	AR 300-46	AR 300-47	AR 300-475			
Applications / conditions	immersion, puddle and spray development 21-23 °C ± 0.5 °C, approx. 40 - 60 s (max. 120 s)							
AR-P 1200, AR-N 2200		2:1 to 3:1	-	-	-			
AR-P 3110, 3120, 3170		-	-	6:1 to 3:1	-			
AR-P 3510, 3540; 3510T, 3540T	ohotoresists	- ; undil.	-	1:1;-	-			
AR-P 3740		-	undil.	pure	-			
AR-BR 5460, 5480		-	-	1:1	-			
AR-N 4340		-	-	-	undil.			
AR-N 4400-10		-	-	3 : 2 to undil.	-			
AR-N 4400-25		1:1	5 : 1 to undil.	undil.	-			
AR-N 4400-50		8 : 1 to undil.	undil.	-	-			
AR-N 7500.18 ; 7500.08	resists	-	-	4 : 1	-			
AR-N 7520.17; 7520.11, .07 new		-	undil.: .17., .11	undil.: .07	-			
AR-N 7520.18 ; 7520.073			-	4 : 1				
AR-N 7700.18 ; 7700.08	e-beam	-	undil. ; 4 : 1	- ; undil.	-			
AR-N 7720.30 ; 7720.13		-	-	undil. ; 4 : 1	-			

## Information on developer processing (→ see also information on developers AR 300-26 and 300-35)

If metal ion-free developers are diluted, it is recommended to adjust the desired normality immediately prior to use by very careful dilution (with scales) of the stronger developer with DI water. Even small differences in normality may cause larger differences in the development rate. Developers should be used as fast as possible, since otherwise developer efficacy may be reduced.